Micron Ref. No.: 00-0644

Docket No.: M4065.0434/P434

## **ABSTRACT**

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[0057] A composite barrier layer formed between a glass film and active regions of a memory device is disclosed. The composite barrier layer comprises an oxide layer formed by atomic deposition process and an insulating layer, for example a nitride barrier layer, formed over the oxide layer. The composite barrier layer eliminates the diffusion of impurity atoms from the glass film into the active regions of the device.